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AUTHOR'S RELEVANT PUBLICATIONS

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1. **Kamalaksha Baral**, Prince Kumar Singh, Sanjay Kumar, Sweta Chander, and Satyabrata Jit, "Ultrathin Body Nanowire Hetero-dielectric Stacked Asymmetric Halo Doped Junctionless Accumulation Mode MOSFET for Enhanced Electrical Characteristics and Negative Bias Stability," ***Superlattices and Microstructures,*** vol. 138, Dec.2019.
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5. **Kamalaksha Baral**, Prince Kumar Singh, Sanjay Kumar, Ashish Kumar Singh, and Satyabrata Jit, "A Unified 2-D Quasi-ballistic Model for Nanowire Junctionless Accumulation and Inversion Mode MOSFET," ***Superlattices and Microstructures*** (Communicated)

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